12/00
12/01

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:

a crystalline semiconductor island formed on an insulating surface;

an insulating film formed on the crystalline semiconductor island; and

a first signal line and a second signal line, each of which overlaps the crystalline semiconductor island with the insulating film interposed therebetween,

wherein:

the first signal line and the second signal line are connected to each other through a metal wiring line, and

the metal wiring line at least partially overlaps the crystalline semiconductor island.

2. (Original) A device according to claim 1, wherein the first signal line and the second signal line are gate signal lines.

3. (Original) A device according to claim 1, wherein the first signal line and the second signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

4. (Previously Presented) A device according to claim 1, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

5. (Previously Presented) A device according to claim 1, wherein the first signal line and the second signal line are spaced apart from each other so that the first signal line and the

crystalline semiconductor island sandwich the insulating film and the second signal line and the crystalline semiconductor island sandwich the insulating film, respectively.

6. (Original) A device according to claim 5, wherein the first signal line and the second signal line are gate signal lines.

7. (Original) A device according to claim 5, wherein the first signal line and the second signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

8. (Previously Presented) A device according to claim 5, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

9. (Original) A device according to claim 1, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

10. (Previously Presented) The semiconductor device according to claim 1, the semiconductor device further comprising a pixel region and at least one driving circuit portion, wherein:

the crystalline semiconductor island, the insulating film, the first signal line, and the second signal line together comprise a first protective circuit; and

the first protective circuit is provided between the driving circuit and the pixel region.

11. (Original) A device according to claim 10, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a

digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

12. (Previously Presented) The semiconductor device according to claim 10, wherein:
the first protective circuit is provided between a second protective circuit and the pixel region.

13. (Original) A device according to claim 12, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

14-20. (Canceled)

21. (Previously Presented) A semiconductor device comprising:
a semiconductor island formed over an insulating surface;
a first insulating film formed over the semiconductor island; and
a first signal line and a second signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween,
wherein:
the first signal line and the second signal line are connected to each other through a metal wiring line, and
the metal wiring line at least partially overlaps the semiconductor island.

22. (Previously Presented) A semiconductor device according to claim 21, wherein the semiconductor island comprises a crystalline semiconductor island.

23. (Previously Presented) A semiconductor device according to claim 22, further comprising a second insulating film formed over the first and second lines, wherein the metal wiring line is formed over the second insulating film.

24. (Previously Presented) A semiconductor device according to claim 21, further comprising a second insulating film formed over the first and second lines, wherein the metal wiring line is formed over the second insulating film.

25. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first signal line and a second signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein:

the first signal line is connected to the second circuit and the second signal line is connected to the third circuit, and

the metal wiring line at least partially overlaps the semiconductor island.

26. (Previously Presented) A semiconductor device according to claim 25, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

27. (Previously Presented) A semiconductor device according to claim 25, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

28. (Previously Presented) A semiconductor device according to claim 25, wherein the first and second signal lines are gate signal lines.

29. (Previously Presented) A semiconductor device according to claim 25, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

30. (Previously Presented) A semiconductor device according to claim 25, further comprising a second insulating film formed over the first and second signal lines, wherein the metal wiring line is formed over the second insulating film.

31. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first signal line and a second signal line, each of which overlaps the first semiconductor island with the first insulating film interposed therebetween, and

a first metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising:

a second semiconductor island formed over the insulating surface,

a second insulating film formed over the semiconductor island,

a third signal line and a fourth signal line, each of which overlaps the second semiconductor island with the second insulating film interposed therebetween, and

a second metal wiring line electrically connecting the third signal line and the fourth signal line;

a third circuit comprising a transistor; and

a fourth circuit comprising a transistor;

wherein:

the first signal line is connected to the third circuit, the second signal line is connected to the third signal line, and the fourth signal line is connected to the fourth circuit, and

the first metal wiring line at least partially overlaps the semiconductor island.

32. (Previously Presented) A semiconductor device according to claim 31, wherein the first and second metal wiring lines extend in a direction parallel to a direction in which the first and fourth signal lines extend.

33. (Previously Presented) A semiconductor device according to claim 31, wherein the first and second metal wiring lines extend in a direction perpendicular to a direction in which the first and fourth signal lines extend.

34. (Previously Presented) A semiconductor device according to claim 31, wherein the third circuit is a pixel portion and the fourth circuit is a driving circuit for driving the pixel portion.

35. (Previously Presented) A semiconductor device according to claim 31, wherein the third circuit is a pixel portion and the fourth circuit is a protective circuit.

36. (Previously Presented) A semiconductor device according to claim 31, wherein the first and fourth signal lines are gate signal lines.

37. (Previously Presented) A semiconductor device according to claim 31, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

38. (Previously Presented) A semiconductor device according to claim 31, further comprising:

a third insulating film formed over the first and second signal lines, and

a fourth insulating film formed over the third and fourth signal lines,

wherein the first metal wiring line is formed over the third insulating film and the second metal wiring line is formed over the fourth insulating film.

39. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a second semiconductor island formed over the insulating surface,

a first insulating film formed over the first and second semiconductor islands,

a first signal line that partially overlaps the first semiconductor island with the first insulating film interposed therebetween,

a second signal line that partially overlaps the second semiconductor island with the first insulating film interposed therebetween,

a third signal line that partially overlaps the first and second semiconductor islands with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein:

the first signal line is connected to the second circuit and the second signal line is connected to the third circuit, and

the metal wiring line at least partially overlaps the first and second semiconductor islands.

40. (Previously Presented) A semiconductor device according to claim 39, wherein the metal wiring line extends in a direction perpendicular to a direction in which the first and second signal lines extend.

41. (Previously Presented) A semiconductor device according to claim 39, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

42. (Previously Presented) A semiconductor device according to claim 39, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

43. (Previously Presented) A semiconductor device according to claim 39, wherein the first and second signal lines are gate signal lines.

44. (Previously Presented) A semiconductor device according to claim 39, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

45. (Previously Presented) A semiconductor device according to claim 39, further comprising a second insulating film formed over the first and second signal lines, wherein the metal wiring line is formed over the second insulating film.

46. (Previously Presented) A semiconductor device comprising:

a crystalline semiconductor island formed on an insulating surface;

an insulating film formed on the crystalline semiconductor island; and

a first metal signal line and a second metal signal, each of which overlaps the crystalline semiconductor island with the insulating film interposed therebetween,

wherein the first metal signal line and the second metal signal line are connected to each other through a metal wiring line.

47. (Previously Presented) A device according to claim 46, wherein the first metal signal line and the second metal signal line are gate signal lines.

48. (Previously Presented) A device according to claim 46, wherein the first metal signal line and the second metal signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

49. (Previously Presented) A device according to claim 46, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

50. (Previously Presented) A device according to claim 46, wherein the first metal signal line and the second metal signal line are spaced apart from each other so that the first metal signal line and the crystalline semiconductor island sandwich the insulating film and the second metal signal line and the crystalline semiconductor island sandwich the insulating film.

51. (Previously Presented) A device according to claim 50, wherein the first metal signal line and the second metal signal line are gate signal lines.

52. (Previously Presented) A device according to claim 50, wherein the first metal signal line and the second metal signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

53. (Previously Presented) A device according to claim 50, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

54. (Previously Presented) A device according to claim 46, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

55. (Previously Presented) The semiconductor device according to claim 46, the semiconductor device further comprising a pixel region and at least one driving circuit portion, wherein:

the crystalline semiconductor island, the insulating film, the first metal signal line, and the second metal signal line together comprise a first protective circuit; and

the protective circuit is provided between the driving circuit and the pixel region.

56. (Previously Presented) A device according to claim 55, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

57. (Previously Presented) The semiconductor device according to claim 55, wherein:

the first protective circuit is provided between a second protective circuit and the pixel region.

58. (Previously Presented) A device according to claim 57, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

59. (Previously Presented) A semiconductor device comprising:

a semiconductor island formed over an insulating surface;

a first insulating film formed over the semiconductor island; and

a first metal signal line and a second metal signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween,

wherein the first metal signal line and the second metal signal line are connected to each other through a metal wiring line.

60. (Previously Presented) A semiconductor device according to claim 59, wherein the semiconductor island comprises a crystalline semiconductor island.

61. (Previously Presented) A semiconductor device according to claim 60, further comprising a second insulating film formed over the first and second metal signal lines, wherein the metal wiring line is formed over the second insulating film.

62. (Previously Presented) A semiconductor device according to claim 59, further comprising a second insulating film formed over the first and second metal signal lines, wherein the metal wiring line is formed over the second insulating film.

63. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first metal signal line and a second metal signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first metal signal line and the second metal signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein the first metal signal line is connected to the second circuit and the second metal signal line is connected to the third circuit.

64. (Previously Presented) A semiconductor device according to claim 63, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

65. (Previously Presented) A semiconductor device according to claim 63, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

66. (Previously Presented) A semiconductor device according to claim 63, wherein the first and second metal signal lines are gate signal lines.

67. (Previously Presented) A semiconductor device according to claim 63, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

68. (Previously Presented) A semiconductor device according to claim 63, further comprising a second insulating film formed over the first and second metal signal lines, wherein the metal wiring line is formed over the second insulating film.

69. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first metal signal line and a second metal signal line, each of which overlaps the first semiconductor island with the first insulating film interposed therebetween, and

a first metal wiring line electrically connecting the first metal signal line and the second metal signal line;

a second circuit comprising:

a second semiconductor island formed over the insulating surface,

a second insulating film formed over the semiconductor island,

a third metal signal line and a fourth metal signal line, each of which overlaps the second semiconductor island with the second insulating film interposed therebetween, and

a second metal wiring line electrically connecting the third metal signal line and the fourth metal signal line;

a third circuit comprising a transistor;

a fourth circuit comprising a transistor;

wherein the first metal signal line is connected to the third circuit, the second metal signal line is connected to the third metal signal line, and the fourth metal signal line is connected to the fourth circuit.

70. (Previously Presented) A semiconductor device according to claim 69, wherein the first and second metal wiring lines extend in a direction parallel to a direction in which the first and fourth metal signal lines extend.

71. (Previously Presented) A semiconductor device according to claim 69, wherein the first and second metal wiring lines extend in a direction perpendicular to a direction in which the first and fourth metal signal lines extend.

72. (Previously Presented) A semiconductor device according to claim 69, wherein the third circuit is a pixel portion and the fourth circuit is a driving circuit for driving the pixel portion.

73. (Previously Presented) A semiconductor device according to claim 69, wherein the third circuit is a pixel portion and the fourth circuit is a protective circuit.

74. (Previously Presented) A semiconductor device according to claim 69, wherein the first and fourth metal signal lines are gate signal lines.

75. (Previously Presented) A semiconductor device according to claim 69, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

76. (Previously Presented) A semiconductor device according to claim 69, further comprising:

a third insulating film formed over the first and second metal signal lines, and

a fourth insulating film formed over the third and fourth metal signal lines,

wherein the first metal wiring line is formed over the third insulating film and the second metal wiring line is formed over the fourth insulating film.

77. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a second semiconductor island formed over the insulating surface,

a first insulating film formed over the first and second semiconductor islands,

a first metal signal line that partially overlaps the first semiconductor island with the first insulating film interposed therebetween,

a second metal signal line that partially overlaps the second semiconductor island with the first insulating film interposed therebetween,

a third metal signal line that partially overlaps the first and second semiconductor islands with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first metal signal line and the second metal signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein the first metal signal line is connected to the second circuit and the second metal signal line is connected to the third circuit.

78. (Previously Presented) A semiconductor device according to claim 77, wherein the metal wiring line extends in a direction perpendicular to a direction in which the first and second metal signal lines extend.

79. (Previously Presented) A semiconductor device according to claim 77, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

80. (Previously Presented) A semiconductor device according to claim 77, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

81. (Previously Presented) A semiconductor device according to claim 77, wherein the first and second metal signal lines are gate signal lines.

82. (Previously Presented) A semiconductor device according to claim 77, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

83. (Previously Presented) A semiconductor device according to claim 77, further comprising a second insulating film formed over the first and second metal signal lines, wherein the metal wiring line is formed over the second insulating film.

84. (Previously Presented) A semiconductor device comprising:

a crystalline semiconductor island formed on an insulating surface;

an insulating film formed on the crystalline semiconductor island; and

a first signal line and a second signal, each of which overlaps the crystalline semiconductor island with the insulating film interposed therebetween,

wherein:

the first signal line and the second signal line are connected to each other through a metal wiring line, and

the crystalline semiconductor island is interposed between the first signal line and the second signal line.

85. (Previously Presented) A device according to claim 84, wherein the first signal line and the second signal line are gate signal lines.

86. (Previously Presented) A device according to claim 84, wherein the first signal line and the second signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

87. (Previously Presented) A device according to claim 84, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

88. (Previously Presented) A device according to claim 84, wherein the first signal line and the second signal line are spaced apart from each other so that the first signal line and the crystalline semiconductor island sandwich the insulating film and the second signal line and the crystalline semiconductor island sandwich the insulating film, respectively.

89. (Previously Presented) A device according to claim 88, wherein the first signal line and the second signal line are gate signal lines.

90. (Previously Presented) A device according to claim 88, wherein the first signal line and the second signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

91. (Previously Presented) A device according to claim 88, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

92. (Previously Presented) A device according to claim 84, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

93. (Previously Presented) The semiconductor device according to claim 84, the semiconductor device further comprising a pixel region and at least one driving circuit portion, wherein:

the crystalline semiconductor island, the insulating film, the first signal line, and the second signal line together comprise a first protective circuit; and

the protective circuit is provided between the driving circuit and the pixel region.

94. (Previously Presented) A device according to claim 93, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

95. (Previously Presented) The semiconductor device according to claim 93, wherein:

the first protective circuit is provided between a second protective circuit and the pixel region.

96. (Previously Presented) A device according to claim 95, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

97. (Previously Presented) A semiconductor device comprising:

a semiconductor island formed over an insulating surface;

a first insulating film formed over the semiconductor island; and

a first signal line and a second signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween,

wherein:

the first signal line and the second signal line are connected to each other through a metal wiring line, and

the semiconductor island is interposed between the first signal line and the second signal line.

98. (Previously Presented) A semiconductor device according to claim 97, wherein the semiconductor island comprises a crystalline semiconductor island.

99. (Previously Presented) A semiconductor device according to claim 98, further comprising a second insulating film formed over the first and second lines, wherein the metal wiring line is formed over the second insulating film.

100. (Previously Presented) A semiconductor device according to claim 97, further comprising a second insulating film formed over the first and second lines, wherein the metal wiring line is formed over the second insulating film.

101. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first signal line and a second signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein:

the first signal line is connected to the second circuit and the second signal line is connected to the third circuit, and

the semiconductor island is interposed between the first signal line and the second signal line.

102. (Previously Presented) A semiconductor device according to claim 101, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

103. (Previously Presented) A semiconductor device according to claim 101, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

104. (Previously Presented) A semiconductor device according to claim 101, wherein the first and second signal lines are gate signal lines.

105. (Previously Presented) A semiconductor device according to claim 101, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

106. (Previously Presented) A semiconductor device according to claim 101, further comprising a second insulating film formed over the first and second signal lines, wherein the metal wiring line is formed over the second insulating film.

107. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first signal line and a second signal line, each of which overlaps the first semiconductor island with the first insulating film interposed therebetween, and

a first metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising:

a second semiconductor island formed over the insulating surface,

a second insulating film formed over the semiconductor island,

a third signal line and a fourth signal line, each of which overlaps the second semiconductor island with the second insulating film interposed therebetween, and

a second metal wiring line electrically connecting the third signal line and the fourth signal line;

a third circuit comprising a transistor;

a fourth circuit comprising a transistor;

wherein:

the first signal line is connected to the third circuit, the second signal line is connected to the third signal line, and the fourth signal line is connected to the fourth circuit, and

the first semiconductor island is interposed between the first signal line and the second signal line.

108. (Previously Presented) A semiconductor device according to claim 107, wherein the first and second metal wiring lines extend in a direction parallel to a direction in which the first and fourth signal lines extend.

109. (Previously Presented) A semiconductor device according to claim 107, wherein the first and second metal wiring lines extend in a direction perpendicular to a direction in which the first and fourth signal lines extend.

110. (Previously Presented) A semiconductor device according to claim 107, wherein the third circuit is a pixel portion and the fourth circuit is a driving circuit for driving the pixel portion.

111. (Previously Presented) A semiconductor device according to claim 107, wherein the third circuit is a pixel portion and the fourth circuit is a protective circuit.

112. (Previously Presented) A semiconductor device according to claim 107, wherein the first and fourth signal lines are gate signal lines.

113. (Previously Presented) A semiconductor device according to claim 107, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

114. (Previously Presented) A semiconductor device according to claim 107, further comprising:

a third insulating film formed over the first and second signal lines, and

a fourth insulating film formed over the third and fourth signal lines,

wherein the first metal wiring line is formed over the third insulating film and the second metal wiring line is formed over the fourth insulating film.

115. (Previously Presented) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a second semiconductor island formed over the insulating surface,

a first insulating film formed over the first and second semiconductor islands,

a first signal line that partially overlaps the first semiconductor island with the first insulating film interposed therebetween,

a second signal line that partially overlaps the second semiconductor island with the first insulating film interposed therebetween,

a third signal line that partially overlaps the first and second semiconductor islands with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein:

the first signal line is connected to the second circuit and the second signal line is connected to the third circuit, and

the first and second semiconductor islands are interposed between the first signal line and the second signal line.

116. (Previously Presented) A semiconductor device according to claim 115, wherein the metal wiring line extends in a direction perpendicular to a direction in which the first and second signal lines extend.

117. (Previously Presented) A semiconductor device according to claim 115, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

118. (Previously Presented) A semiconductor device according to claim 115, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

119. (Previously Presented) A semiconductor device according to claim 115, wherein the first and second signal lines are gate signal lines.

120. (Previously Presented) A semiconductor device according to claim 115, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

121. (Previously Presented) A semiconductor device according to claim 115, further comprising a second insulating film formed over the first and second signal lines, wherein the metal wiring line is formed over the second insulating film.